

Photocouplers GaAlAs Infrared LED & Photo IC

TLP2301

1. Applications

- · Industrial Inverters
- · Communications Equipment
- · Home Electric Appliances

2. General

The Toshiba TLP2301 consists of a high-speed detector based on the photo-transistor optically coupled to GaAlAs infrared emitting diodes. It is housed in the SO6 package. The TLP2301 has realized the early switching characteristics by several $k\Omega$ resistance. The TLP2301 correspond to the transmission rate of 20 kbps, and has become a product which fills between a general-purpose transistor coupler and IC couplers corresponding to 1 Mbps.

3. Features

- (1) Collector-emitter voltage: 40 V (min)
- (2) Current transfer ratio: 50% (min) (@ $I_F = 1$ mA, $V_{CE} = 5$ V) Rank GB: 100% (min) (@ $I_F = 1$ mA, $V_{CE} = 5$ V)
- (3) Isolation voltage: 3750 Vrms (min)
- (4) Propagation delay time: t_{pHL} = 30 μs (max), t_{pLH} = 30 μs (max) @ I_F = 1 mA, R_L = 10 $k\Omega$, T_a = 25 °C
- (5) Operating temperature: -55 to 125 °C
- (6) Safety standards

UL-approved: UL1577, File No.E67349

cUL-approved: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN60747-5-5, EN60065 or EN60950-1 (Note 1)

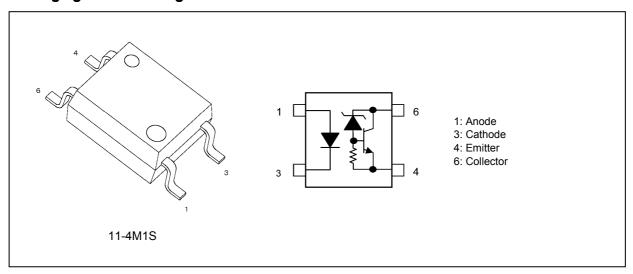
CQC-approved: GB4943.1, GB8898 Thailand Factory



仅适用干海拔 2000m 以下地区安全使用

Note 1: When a VDE approved type is needed, please designate the Option (V4).

4. Packaging and Pin Assignment



Start of commercial production



5. Principle of Operation

5.1. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	5.0	mm
Clearance	5.0	
Internal isolation thickness	0.4	

6. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics	Characteristics				Unit
LED	Input forward current		I _F		50	mA
	Input forward current derating	(T _a ≥ 90 °C)	$\Delta I_F/\Delta T_a$		-1.11	mA/°C
	Input forward current (pulsed)		I _{FP}	(Note 1)	1	Α
	Input reverse voltage	,	V _R		5	V
	Input power dissipation		P _D		100	mW
	Input power dissipation derating	$(T_a \ge 90 \text{ °C})$	$\Delta P_D/\Delta T_a$		-2.8	mW/°C
	Junction temperature		T _j		135	°C
Detector	Collector-emitter voltage		V _{CEO}		40	V
	Emitter-collector voltage		V _{ECO}		7	V
	Collector current		I _C		50	mA
	Collector power dissipation		P _C		150	mW
	Collector power dissipation derating	(T _a ≥ 25 °C)	$\Delta P_{C}/\Delta T_{a}$		-1.35	mW/°C
	Junction temperature		Tj		135	°C
Common	Operating temperature		T _{opr}		-55 to 125	
	Storage temperature		T _{stg}		-55 to 125	
	Lead soldering temperature	(10 s)	T _{sol}		260	°C
	Total power dissipation		P _T		200	mW
Common	Isolation voltage	AC, 60 s, R.H. ≤ 60%	BV _S	(Note 2)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) \leq 0.1 ms, f = 100 Hz

Note 2: This device is considered as a two-terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.



7. Electrical Characteristics (Unless otherwise specified, Ta = 25 °C)

	Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
LED	Input forward voltage	V _F		I _F = 10 mA	1.1	1.25	1.4	V
	Input reverse current	I _R		V _R = 5 V	_	_	10	μА
	Input capacitance	Ct		V = 0 V, f = 1 MHz	_	30		pF
Detector	Collector-emitter breakdown voltage	V _{(BR)CEO}		I _C = 0.1 mA	40			V
	Emitter-collector breakdown voltage	V _{(BR)ECO}		I _E = 0.1 mA	7			
	Dark Current	I _{DARK}		V _{CE} = 40 V	_	0.01	0.08	μА
				V _{CE} = 40 V, T _a = 85 °C	_	2	50	
	Collector-emitter capacitance	C _{CE}		V = 0 V, f = 1 MHz	_	10		pF

8. Coupled Electrical Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	I _C /I _F	(Note1)	I _F = 1 mA, V _{CE} = 5 V	50	1	600	%
			I_F = 1 mA, V_{CE} = 5 V, Rank GB	100		600	
Saturated current transfer ratio	I _C /I _{F(sat)}		$I_F = 1 \text{ mA}, V_{CE} = 0.3 \text{ V}$		100		
			I_F = 1 mA, V_{CE} = 0.3 V, Rank GB	50			
Collector-emitter saturation voltage	V _{CE(sat)}		I _C = 2.4 mA, I _F = 8 mA			0.3	V
			$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$	_	0.2	_	
			$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}, \text{ Rank GB}$			0.3	
OFF-state collector current	I _{C(off)}		$V_F = 0.7 \text{ V}, V_{CE} = 40 \text{ V}$	_	1	10	μΑ

Note1: See Table 9.1 for current transfer ratio.

Table 9.1 Current Transfer Ratio (CTR) Rank (Note) (Unless otherwise specified, Ta = 25 °C)

Rank	Test Condition	Current transfer ratio I _C /I _F Min	Current transfer ratio I _C /I _F Max	Unit
None	I _F = 1 mA, V _{CE} = 5 V	50	600	%
GB		100	600	

Note: Specify both the part number and a rank in this format when ordering.

Example: TLP2301(GB)

For safety standard certification, however, specify the part number alone.

Example: TLP2301(GB,E: TLP2301

9. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Total capacitance (input to output)	Cs	(Note 1)	V _S = 0 V, f = 1 MHz		8.0		pF
Isolation resistance	R _S	(Note 1)	V _S = 500 V, R.H. ≤ 60%	1 × 10 ¹²	1014		Ω
Isolation voltage	BVS	(Note 1)	AC, 60 s	3750			Vrms
			AC, 1 s in oil	_	10000		
			DC, 60 s in oil	_	10000	_	Vdc

Note 1: This device is considered as a two-terminal device: 1 and 3 are shorted together, and pins 4 and 6 are shorted together.



10. Switching Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}		See figure 10.1 V_{CC} = 5 V, I_F = 1 mA, R_L = 10 k Ω		15	30	μS
Propagation delay time (L/H)	t _{pLH}		See figure 10.1 V_{CC} = 5 V, I_F = 1 mA, R_L = 10 k Ω	-	8	30	μS

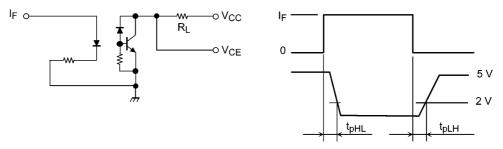
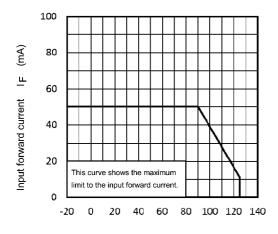


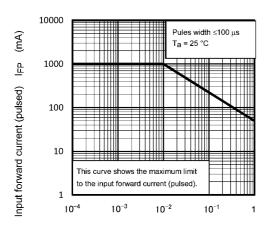
Fig. 10.1 Propagation delay Time Test Circuit

11. Characteristics Curves (Note)

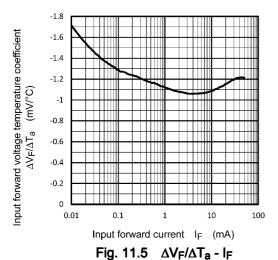


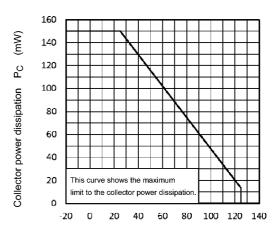
Ambient temperature Ta (°C)

Fig. 11.1 $I_F - T_a$



Duty cycle ratio DR Fig. 11.3 IFP - DR





Ambient temperature T_a (°C)

Fig. 11.2 P_C - T_a

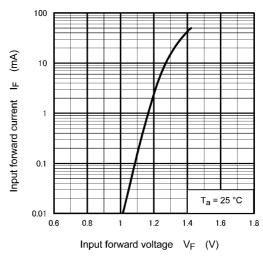


Fig. 11.4 I_F - V_F

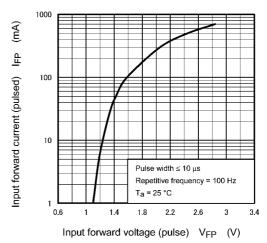


Fig. 11.6 IFP - VFP

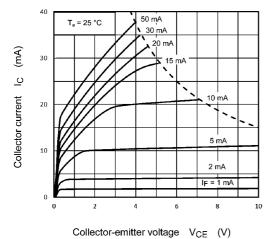


Fig. 11.7 I_C - V_{CE}

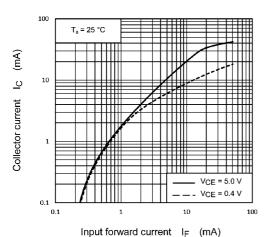


Fig. 11.9 I_C - I_F

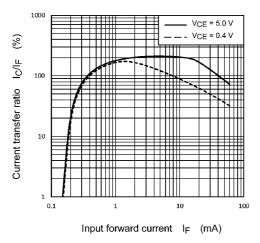
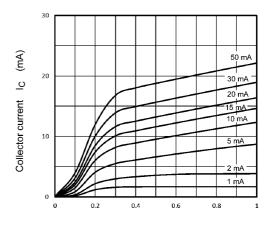


Fig. 11.11 I_C/I_F - I_F



Collector-emitter voltage V_{CE} (V) Fig. 11.8 I_C - V_{CE}

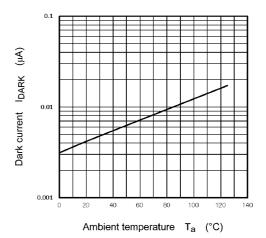


Fig. 11.10 I_{DARK} - T_a

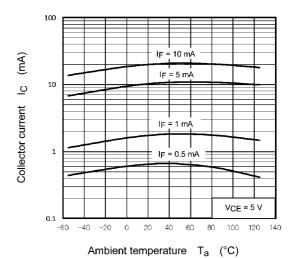


Fig. 11.12 I_C - T_a

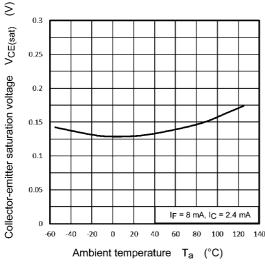


Fig. 11.13 V_{CE(sat)} - T_a

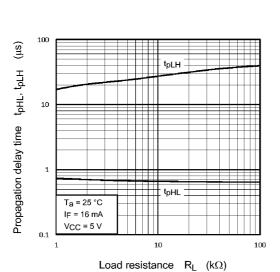


Fig. 11.15 t_{pHL},t_{pLH} - R_L

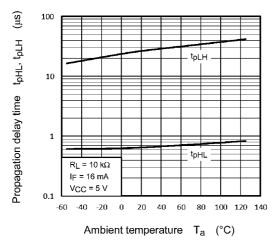


Fig. 11.17 t_{pHL} , t_{pLH} - T_a

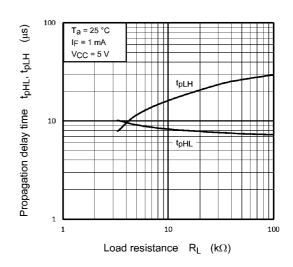


Fig. 11.14 t_{pHL},t_{pLH} - R_L

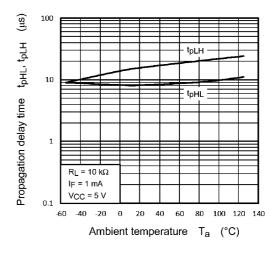


Fig. 11.16 t_{pHL},t_{pLH} - T_a

ote: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



12. Soldering and Storage

12.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

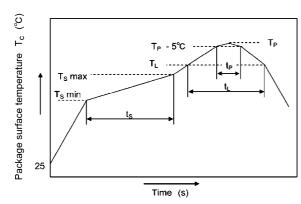
· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	s
Ramp-up rate (T _L to T _P)			3	°C/s
Liquidus temperature	TL	217		°C
Time above T _L	t∟	60	150	s
Peak temperature	T _P		260	°C
Time during which T_c is between $(T_P - 5)$ and T_P	t _P		30	s
Ramp-down rate (T _P to T _L)			6	°C/s

An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

When using soldering flow

Preheat the device at a temperature of 150 $^{\circ}\text{C}$ (package surface temperature) for 60 to 120 seconds.

Mounting condition of 260 °C within 10 seconds is recommended.

Flow soldering must be performed once.

· When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

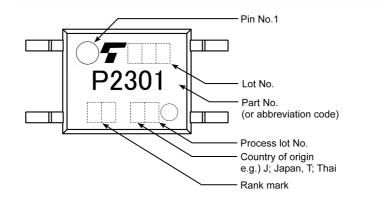
Heating by soldering iron must be done only once per lead.

12.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- · Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.



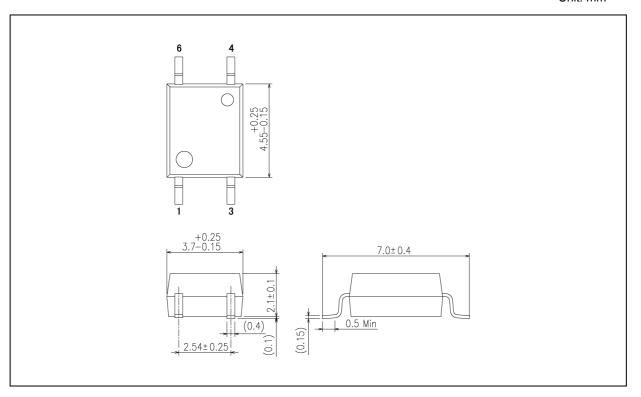
13. Marking





Package Dimensions

Unit: mm



Weight: 0.08 g (typ.)

	Package Name(s)
TOSHIBA: 11-4M1S	



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